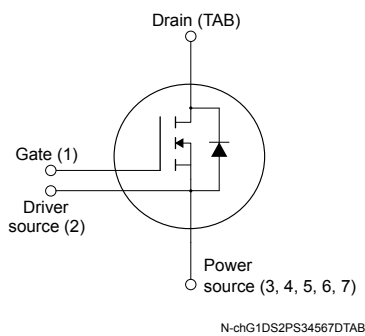
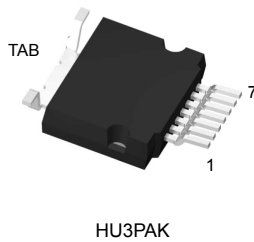



Automotive-grade silicon carbide Power MOSFET 650 V, 58 mΩ typ., 30 A in an HU3PAK package



Features

Order code	V _{DS}	R _{DS(on)} typ.	I _D
SCT055HU65G3AG	650 V	58 mΩ	30 A

- AEC-Q101 qualified 
- Very low R_{DS(on)} over the entire temperature range
- High speed switching performances
- Very fast and robust intrinsic body diode
- Source sensing pin for increased efficiency

Applications

- Main inverter (electric traction)
- DC/DC converter for EV/HEV
- On board charger (OBC)

Description

This silicon carbide Power MOSFET device has been developed using ST's advanced and innovative 3rd generation SiC MOSFET technology. The device features a very low R_{DS(on)} over the entire temperature range combined with low capacitances and very high switching operations, which improve application performance in frequency, energy efficiency, system size and weight reduction.

Product status link

[SCT055HU65G3AG](#)

Product summary

Order code	SCT055HU65G3AG
Marking	SCT55HU65G3AG
Package	HU3PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	-10 to 22	V
	Gate-source voltage (recommended operating values)	-5 to 18	
	Gate-source transient voltage, $t_p < 1 \mu s$, $t \leq 10$ hours over lifetime	-11 to 25	
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25 \text{ }^\circ\text{C}$	30	A
	Drain current (continuous) at $T_C = 100 \text{ }^\circ\text{C}$	30	
$I_{DM}^{(2)}$	Drain current (pulsed)	132	A
P_{TOT}	Total power dissipation at $T_C = 25 \text{ }^\circ\text{C}$	185	W
T_{stg}	Storage temperature range	-55 to 175	$^\circ\text{C}$
T_J	Operating junction temperature range		$^\circ\text{C}$

- I_D is limited by package.
- Pulse width is limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.81	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	50	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = -10\text{ to }22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 1\text{ mA}$	1.8	3.0	4.2	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 15\text{ V}$, $I_D = 15\text{ A}$		76		m Ω
		$V_{GS} = 18\text{ V}$, $I_D = 15\text{ A}$		58	72	
		$V_{GS} = 18\text{ V}$, $I_D = 15\text{ A}$, $T_J = 175\text{ °C}$		69		

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 400\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	721	-	pF
C_{oss}	Output capacitance		-	73	-	pF
C_{riss}	Reverse transfer capacitance		-	11	-	pF
Q_g	Total gate charge	$V_{DD} = 400\text{ V}$, $V_{GS} = -5\text{ to }18\text{ V}$, $I_D = 15\text{ A}$	-	29	-	nC
Q_{gs}	Gate-source charge		-	9	-	nC
Q_{gd}	Gate-drain charge		-	10.7	-	nC
R_g	Gate input resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	1.4	-	Ω

Table 5. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
E_{on}	Turn-on switching energy	$V_{DD} = 400\text{ V}$, $I_D = 15\text{ A}$,	-	27.5	-	μJ
E_{off}	Turn-off switching energy	$R_G = 5.6\text{ }\Omega$, $V_{GS} = -5\text{ V to }18\text{ V}$	-	19.3	-	μJ

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 15\text{ A}$, $R_G = 5.6\text{ }\Omega$, $V_{GS} = -5\text{ to }18\text{ V}$	-	9.2	-	ns
t_r	Rise time		-	7.9	-	ns
$t_{d(off)}$	Turn-off delay time		-	14.2	-	ns
t_f	Fall time		-	12.1	-	ns

Table 7. Reverse SiC diode characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Continuous diode forward current	$T_C = 25\text{ }^\circ\text{C}$	-		30	A
		$T_C = 100\text{ }^\circ\text{C}$	-		30	
V_{SD}	Diode forward voltage	$I_{SD} = 15\text{ A}, V_{GS} = 0\text{ V}$	-	3		V
t_{rr}	Reverse recovery time	$I_{SD} = 15\text{ A}, di/dt = 3000\text{ A}/\mu\text{s},$ $V_{DD} = 400\text{ V}$	-	12		ns
Q_{rr}	Reverse recovery charge		-	132		nC
I_{RRM}	Reverse recovery current		-	18		A

1. I_{SD} is limited by package.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

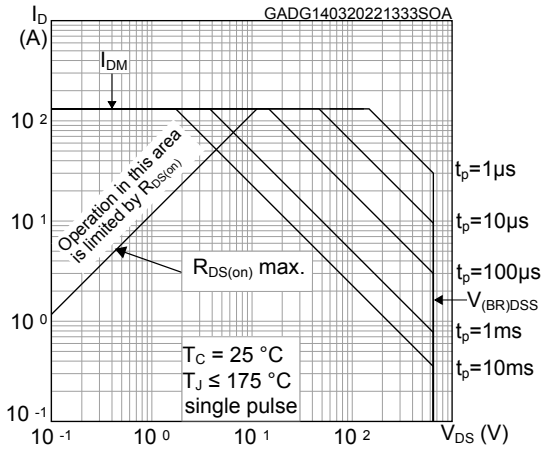


Figure 2. Maximum transient thermal impedance

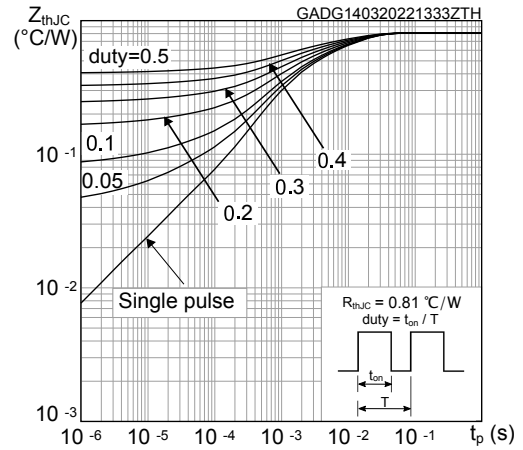


Figure 3. Typical output characteristics ($T_J = 25^\circ\text{C}$)

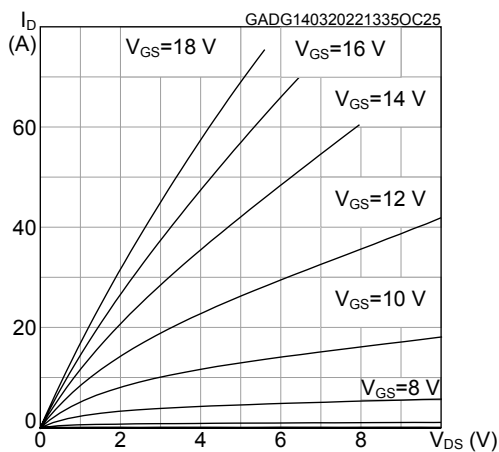


Figure 4. Typical output characteristics ($T_J = 175^\circ\text{C}$)

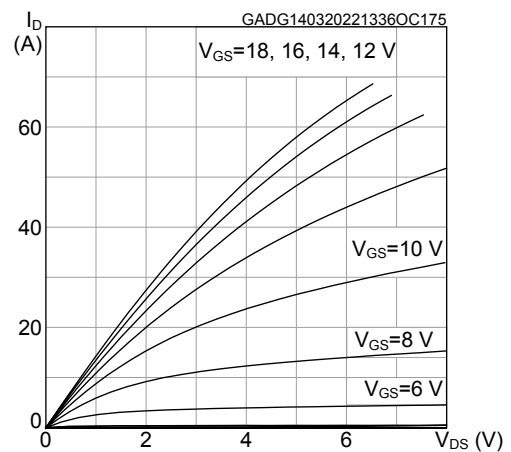


Figure 5. Typical transfer characteristics

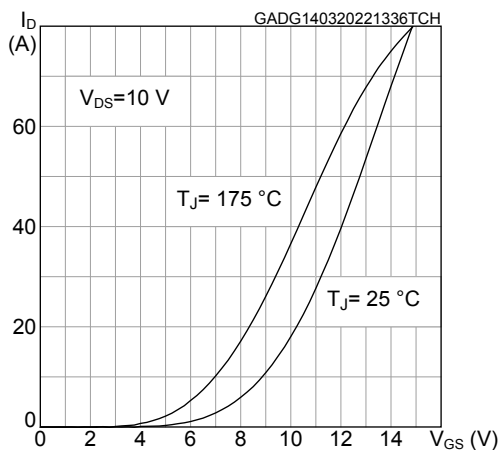


Figure 6. Total power dissipation

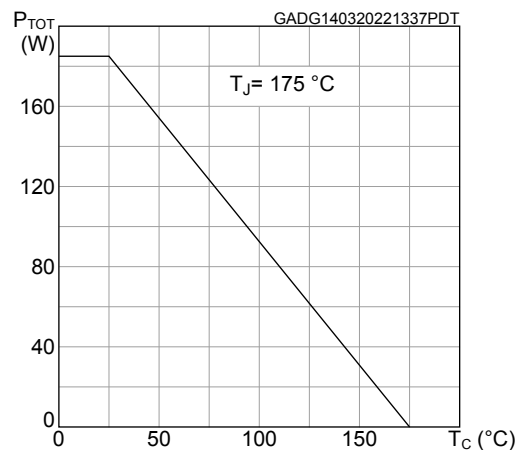


Figure 7. Typical gate charge characteristics

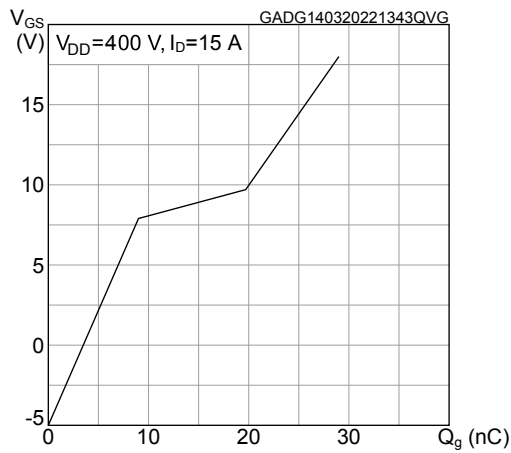


Figure 8. Typical capacitance characteristics

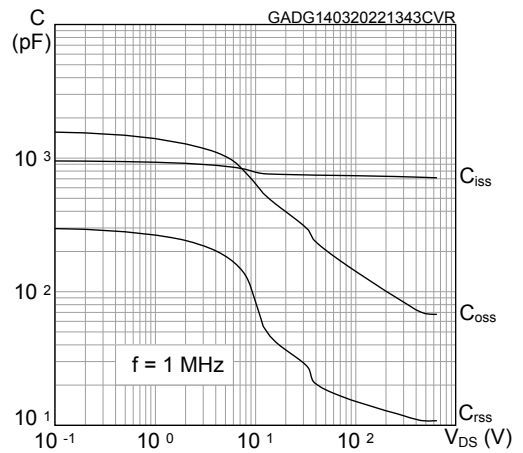


Figure 9. Typical switching energy vs drain current

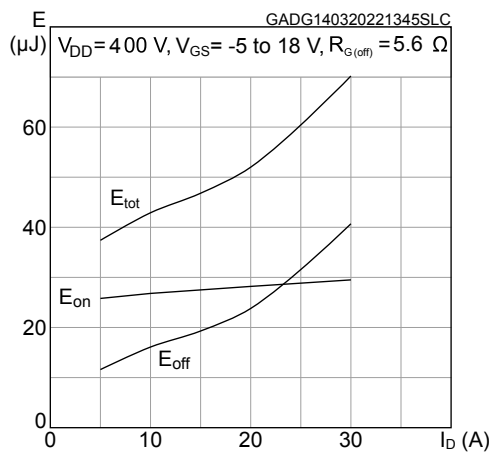


Figure 10. Typical switching energy vs gate resistance

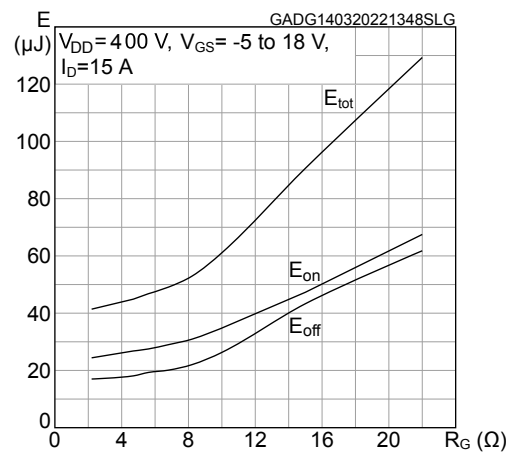


Figure 11. Typical switching energy vs V_DS

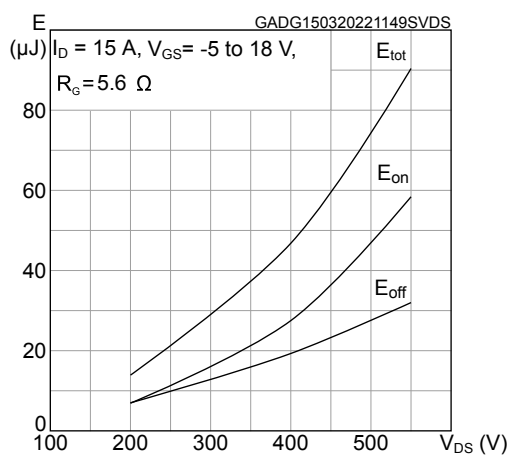


Figure 12. Normalized breakdown voltage vs temperature

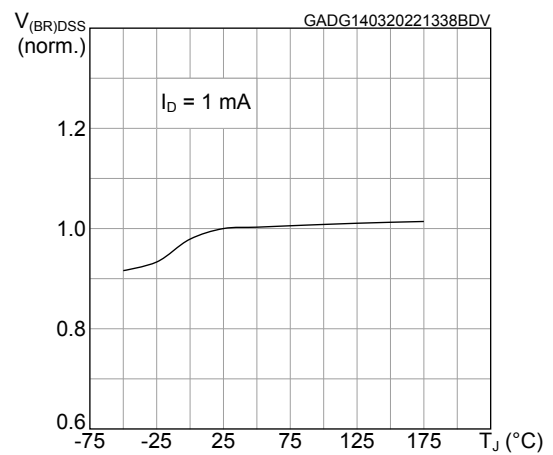


Figure 13. Normalized gate threshold vs temperature

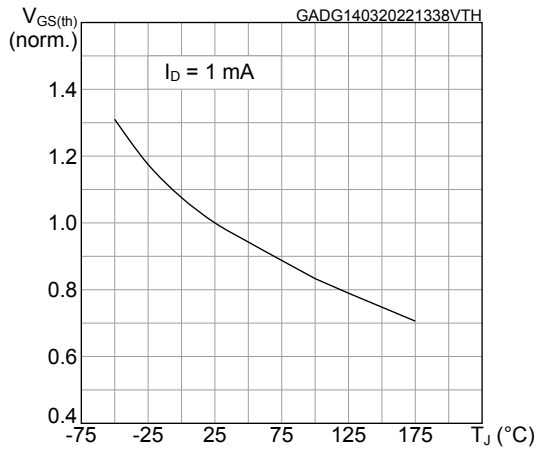


Figure 14. Normalized on-resistance vs temperature

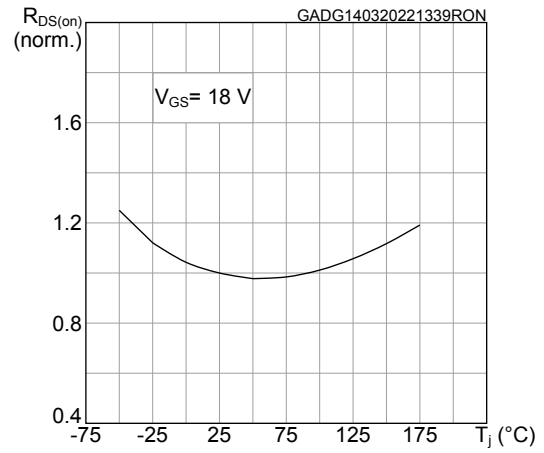


Figure 15. Typical reverse conduction characteristics (T_J= 25°C)

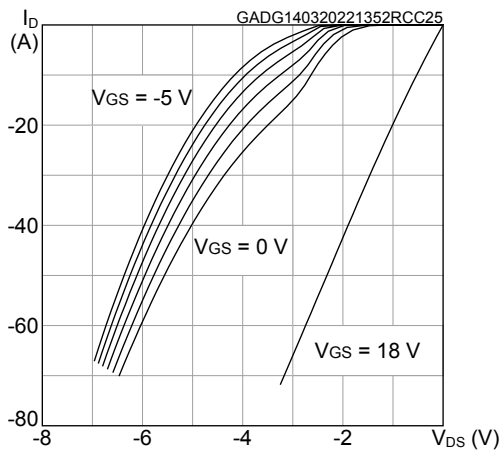
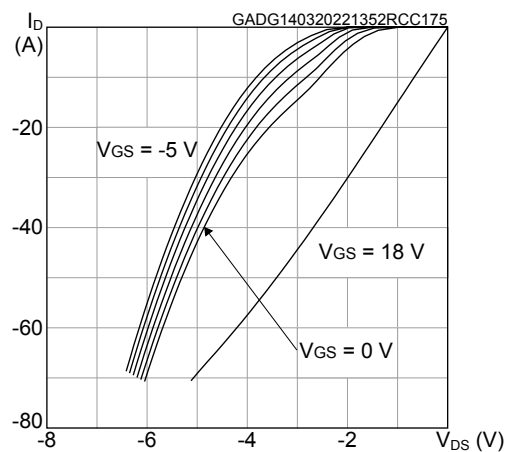


Figure 16. Typical reverse conduction characteristics (T_J= 175°C)

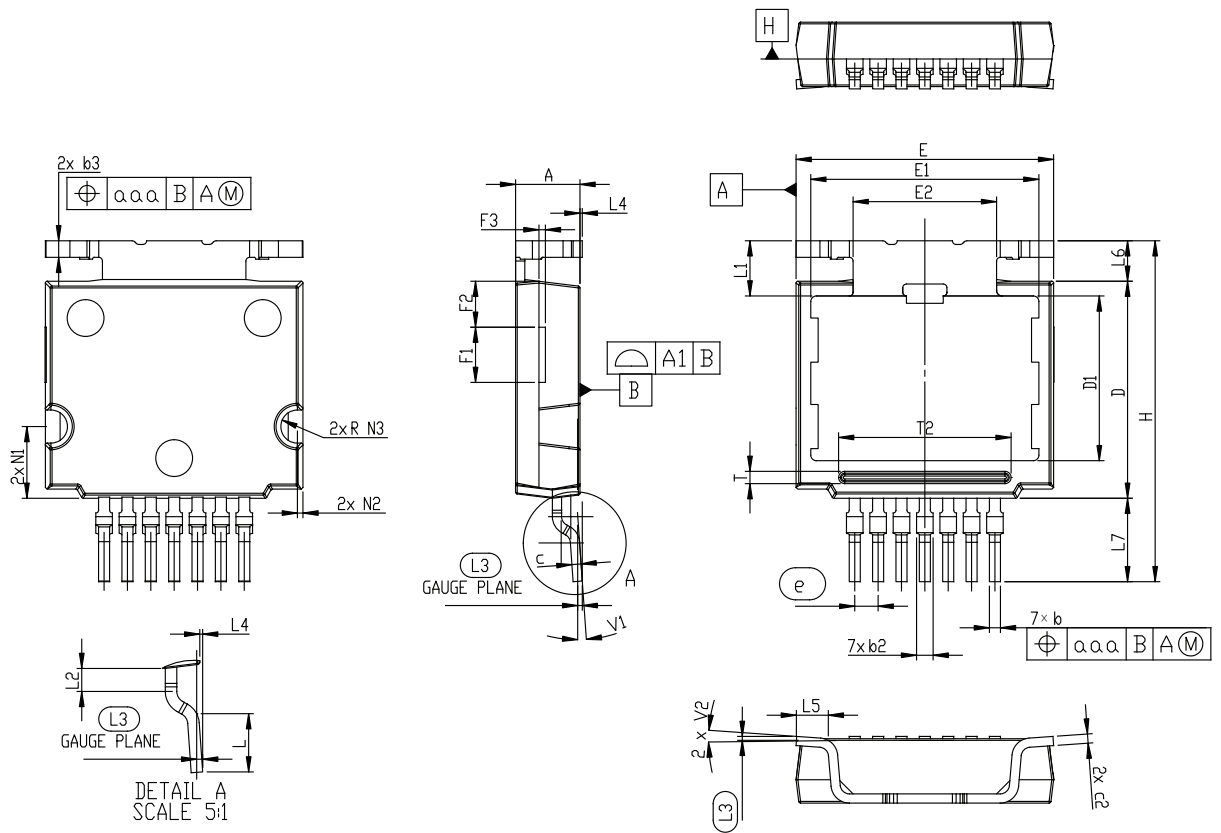


3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

3.1 HU3PAK package information

Figure 17. HU3PAK package outline

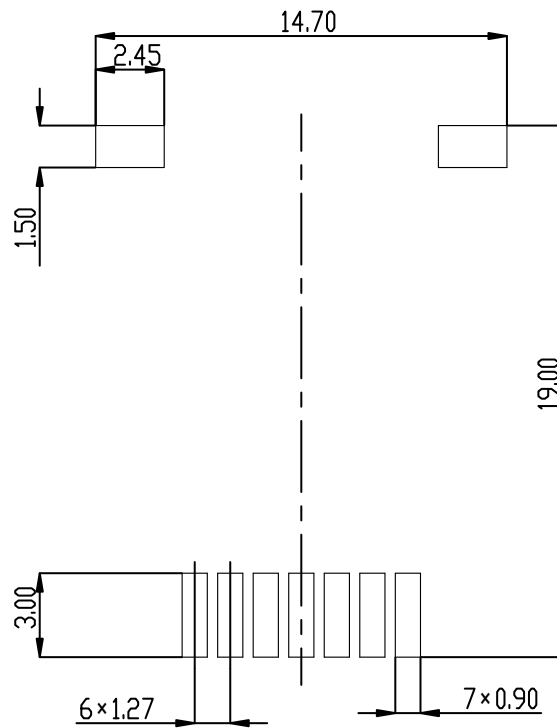


DM00674007_2

Table 8. HU3PAK package mechanical data

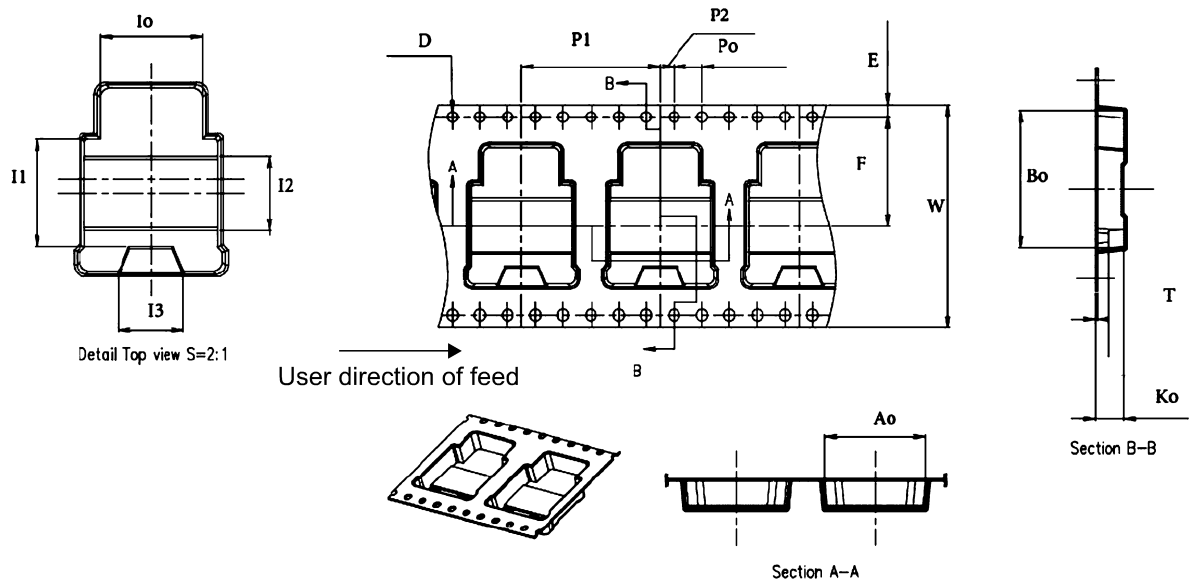
Ref.	Dimensions		
	mm		
	Min.	Typ.	Max.
A	3.40	3.50	3.60
A1		0.05	
b	0.50	0.60	0.70
b2	0.50	0.70	1.00
b3	0.80	0.90	1.00
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	11.70	11.80	11.90
D1	8.80	8.955	9.10
E	13.90	14.00	14.10
E1	12.30	12.40	12.50
E2	7.75	7.80	7.85
e		1.27	
H	18.00	18.58	19.00
aaa		0.10	
L	2.40	2.52	2.60
L1		3.05	
L2	0.90	1.00	1.10
L3		0.26	
L4	0.075	0.125	0.175
L5	1.83	1.93	2.03
L6	2.14	2.24	2.34
L7	4.44	4.54	4.64
F1	2.90	3.00	3.10
F2	2.40	2.50	2.60
F3	0.25	0.35	0.45
N1	3.80	3.90	4.00
N2	0.25	0.30	0.45
N3	0.80	0.90	1.00
T	0.50	0.67	0.70
T2	9.18	9.38	9.43
V1		0°	8°
V2		0°	8°

Figure 18. HU3PAK recommended footprint (dimensions in mm)



3.2 HU3PAK packing information

Figure 19. HU3PAK carrier tape outline



DM00345054_3

Table 9. HU3PAK tape mechanical data

Dimension	Value
	mm
A0	14.40 ±0.10
B0	19.70
D	1.50 ±0.10
E	1.75 ±0.10
F	15.65 ±0.10
I0	11.00
I1	11.60 ±0.10
I2	8.00
I3	7.00
K0	4.20
P0	4.00 ±0.10
P1	20.00 ±0.10
P2	2.00 ±0.10
T	0.40 ±0.50
W	32.00 ±0.30

Figure 20. HU3PAK reel outline

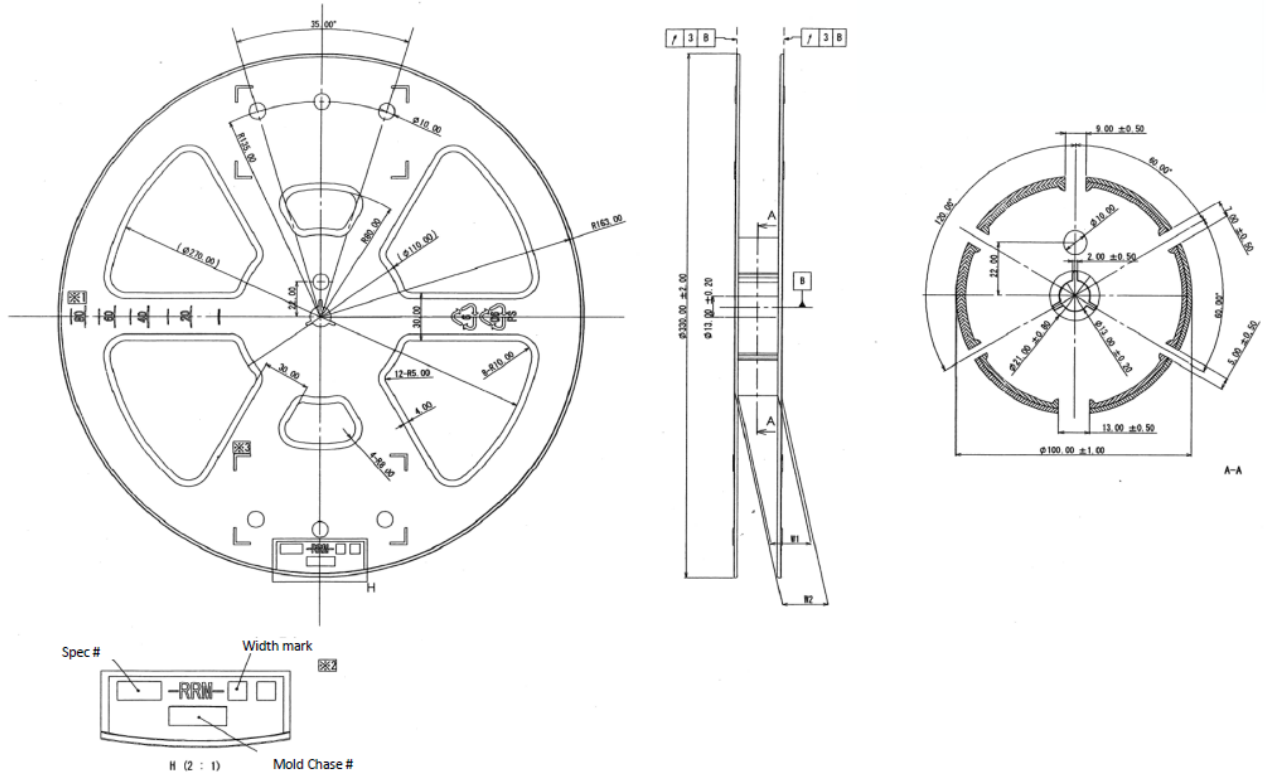


Table 10. HU3PAK reel mechanical data

Dimension	Value
	mm
Reel width	32.0
Reel inner width	33.4 ± 1.0
Reel outer width	37.4 ± 1.0

Revision history

Table 11. Document revision history

Date	Revision	Changes
16-Mar-2022	1	First release.

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3.1	HU3PAK package information	8
3.2	HU3PAK packing information	11
	Revision history	13

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[G3R12MT12K](#) [G3R160MT12D](#) [G3R160MT12J-TR](#) [G3R160MT17D](#) [G3R160MT17J-TR](#) [G3R20MT12K](#) [G3R20MT12N](#) [G3R20MT17K](#)
[G3R20MT17N](#) [G3R30MT12J-TR](#)